

Eamonn Hughes

List of Publications by Year in descending order

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20
papers

627
citations

759055

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940416

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20
docs citations

20
times ranked

460
citing authors

#	ARTICLE	IF	CITATIONS
1	Powder bed binder jet printed alloy 625: Densification, microstructure and mechanical properties. <i>Materials and Design</i> , 2016, 108, 126-135.	3.3	130
2	Microstructural evolution and mechanical properties of differently heat-treated binder jet printed samples from gas- and water-atomized alloy 625 powders. <i>Acta Materialia</i> , 2017, 124, 280-289.	3.8	125
3	High-temperature reliable quantum-dot lasers on Si with misfit and threading dislocation filters. <i>Optica</i> , 2021, 8, 749.	4.8	76
4	Perspectives on Advances in Quantum Dot Lasers and Integration with Si Photonic Integrated Circuits. <i>ACS Photonics</i> , 2021, 8, 2555-2566.	3.2	67
5	A Pathway to Thin GaAs Virtual Substrate on On-axis Si (001) with Ultralow Threading Dislocation Density. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021, 218, 2000402.	0.8	48
6	Defect filtering for thermal expansion induced dislocations in III-V lasers on silicon. <i>Applied Physics Letters</i> , 2020, 117, .	1.5	38
7	Non-radiative recombination at dislocations in InAs quantum dots grown on silicon. <i>Applied Physics Letters</i> , 2019, 115, .	1.5	27
8	Data on the densification during sintering of binder jet printed samples made from water- and gas-atomized alloy 625 powders. <i>Data in Brief</i> , 2017, 10, 116-121.	0.5	26
9	Reduced dislocation growth leads to long lifetime InAs quantum dot lasers on silicon at high temperatures. <i>Applied Physics Letters</i> , 2021, 118, .	1.5	20
10	Interface structure and luminescence properties of epitaxial PbSe films on InAs(111)A. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021, 39, .	0.9	14
11	Defects in Cd3As2 epilayers via molecular beam epitaxy and strategies for reducing them. <i>Physical Review Materials</i> , 2019, 3, .	0.9	14
12	Nucleation control and interface structure of rocksalt PbSe on (001) zincblende III-V surfaces. <i>Physical Review Materials</i> , 2020, 4, .	0.9	14
13	Glide of threading dislocations in (In)AlGaAs on Si induced by carrier recombination: Characteristics, mitigation, and filtering. <i>Journal of Applied Physics</i> , 2019, 125, .	1.1	9
14	Kinetically limited misfit dislocations formed during post-growth cooling in III-V lasers on silicon. <i>Journal Physics D: Applied Physics</i> , 2021, 54, 494001.	1.3	7
15	Epitaxial Integration and Defect Structure of Layered SnSe Films on PbSe/III-V Substrates. <i>Crystal Growth and Design</i> , 0, , .	1.4	5
16	Pipe-diffusion-enriched dislocations and interfaces in SnSe/PbSe heterostructures. <i>Physical Review Materials</i> , 2021, 5, .	0.9	4
17	Bright mid-infrared photoluminescence from high dislocation density epitaxial PbSe films on GaAs. <i>APL Materials</i> , 2021, 9, .	2.2	3
18	High temperature reliable epitaxially grown quantum dot lasers on (001) Si with record performance. , 2021, , .		0

#	ARTICLE	IF	CITATIONS
19	Advances in heteroepitaxial integration of III-V and IV-VI semiconductors with electron channeling contrast imaging. <i>Microscopy and Microanalysis</i> , 2021, 27, 908-910.	0.2	0
20	Degradation Behaviors in InAs Quantum Dot Lasers on Silicon using Misfit Dislocation Trapping Layers. , 2021, , .		0